

EFFECT OF THERMAL ANNEALING ON THE STRUCTURAL AND OPTICAL PROPERTIES OF Ag/As₂S₃ MULTILAYERS*

F. SAVA*, A. LŐRINCZI, A. VELEA, I. D. SIMANDAN, N. PREDA,
G. SOCOL^a, I. N. MIHĂILESCU^a, C. S. ZAMFIRA^b, N.-C. CREȚU^b,
M. POPESCU

National Institute of Materials Physics, Magurele, Bucharest, Atomistilor str. 105 bis, 077125, Ilfov, P. O. Box MG.7, ROMANIA

^aNational Institute for Laser, Plasma and Radiation Physics, P. O. Box M.G. 36, Magurele-Bucharest, RO-077125, Romania

^b“Transilvania” University of Brasov, Faculty of Mechanical Engineering, Precision Mechanics and Mechatronics Department, Brasov, Romania

A complex structure of four double layers of Ag / As₂S₃ has been deposited by Pulsed Laser Deposition method on a glass substrate. The effects of thermal annealing on the structural and optical properties were investigated. An effect of layer mixing has been evidenced.

(Received | July 14, 2013; Accepted November 11, 2013)

Keywords: Chalcogenides; Multilayers; XRR investigation; Silver

1. Introduction

Chalcogenide multilayers are important for integrated optics devices and information recording [1-3]. Extensively studies of optical induced diffusion and dissolution of metals in chalcogenide glasses have been carried out [4-8]. Recently, we have studied the silver diffusion in As₂S₃ thin films produced by green laser light irradiation [9, 10]. During the photodiffusion of silver the intensity of first sharp diffraction peak (FSDP) on the XRD diagram gradually decreases, which can be interpreted by gradually filling with silver of the interstitial voids of the amorphous chalcogenide network (as structural modelling revealed). We have monitored in [10] the photodiffusion of silver by following the degree of transmission of monochromatic red light beam ($\lambda = 635$ nm) through Ag/As₂S₃ double layer. The behaviour of the chalcogenide films under high power laser beam irradiation has been recently studied and discussed in [11]. The papers on thermodiffusion of silver in chalcogenides are scarce [12-16]. The properties of various chalcogenides doped by different amount of silver were investigated in [17-19]. Zuczek et al. [20] have investigated the influence of Ag doping of polymers on the dispersion of hydroxyapatite in aqueous systems.

In this paper we report the results of the study of a multilayer based on alternate layers of Ag and As₂S₃ (four pairs of Ag / As₂S₃ layers) under thermal annealing.

*Paper presented at 6th International Conference on Amorphous and Nanostructured Chalcogenides, Brasov, Romania, June 24-28, 2013

*Corresponding author: fsava@infim.ro

2. Experimental

2.1. Thin films deposition

Ag / As₂S₃ multilayers (four pairs of Ag / As₂S₃ layers) were prepared on glass substrate by pulsed laser deposition (PLD) using a KrF* laser source ($\lambda = 248$ nm, $\tau_{\text{FWHM}} = 25$ ns, power = 70 mW), model COMPexPro 205, Lambda Physics-Coherent. Ag and As₂S₃ targets were subsequently irradiated in the same step by the means of carousel at a laser fluence of 1.5 J/cm² and a repetition rate of 5 Hz. The number of laser pulses applied for deposition of a single silver or arsenic sulphide layer was 7500 and 300, respectively. The depositions were carried out at room temperature while the pressure of the residual gas inside chamber was 4×10^{-4} Pa. In order to obtain homogeneous films, the substrates were rotated during the deposition at a target – substrate distance of 4.5 cm.

2.2. Thermal annealing

The Ag/As₂S₃ multilayer sample was successively thermal annealed for 30 minutes (under nitrogen atmosphere) at 100 °C, 150 °C, 200 °C, 250 °C and 300 °C, respectively.

2.3. X-ray investigation

For X-ray diffraction a Bruker A8 Advanced diffractometer with CuK _{α} target tube and Lynx Eye detector has been used. The X-ray reflectivity (XRR) has been carried out with Bruker A8 Advanced provided with CuK _{α} target tube, scintillation counter, Göbell mirror and Asymmetric Channel-cut (ACC) Ge (220) to get a parallel monochromatic beam. The XRR patterns before and after different temperatures of annealing have been recorded using an angular step of 0.0025° (2θ) and a counting time per step of 10 s.

2.4. Transmission spectroscopy

Optical properties were investigated by transmission spectroscopy. The spectra were recorded using UV-Vis-NIR Carry 5000 spectrophotometer.

3. Results

The XRD pattern of not-annealed multilayer sample shows little modifications upon thermal annealing between 100 ÷ 250 °C (Fig. 1 a ÷ e). After thermal annealing at 300 °C the XRD diagram (Fig. 1 f) shows narrow peaks which could be assigned to crystalline phases: Ag₂S (ASTM file no. 14-0072) and As₂S₃ (ASTM file no. 53-0530).

The X-ray reflectivity (XRR) diagram of the fresh Ag / As₂S₃ multilayered sample is presented in Fig. 2a. The XRR diagram of the multilayer sample changes little after thermal annealing between 100 ÷ 150 °C (Fig. 2 b, c). After thermal annealing at 200 °C an oscillating character of X-ray reflectivity is observed (Fig. 2 d). This is due to the multilayer structure of deposited films (Kossel fringes). From the value of the interfringe we deduced the thickness of one bilayer (147.1 nm) and therefore the thickness of the multilayer are 4×147.1 nm = 588.4 nm. In the same time a nanolayer begins to form. The thickness of this nanolayer increases, reaching 27.7 nm after thermal annealing at 250 °C under nitrogen atmosphere, while the fringes of the multilayer structure disappear (Fig. 2 e). After thermal annealing at 300 °C the sample shows an XRR diagram (Fig. 2 f) corresponding to a thick monolayer.

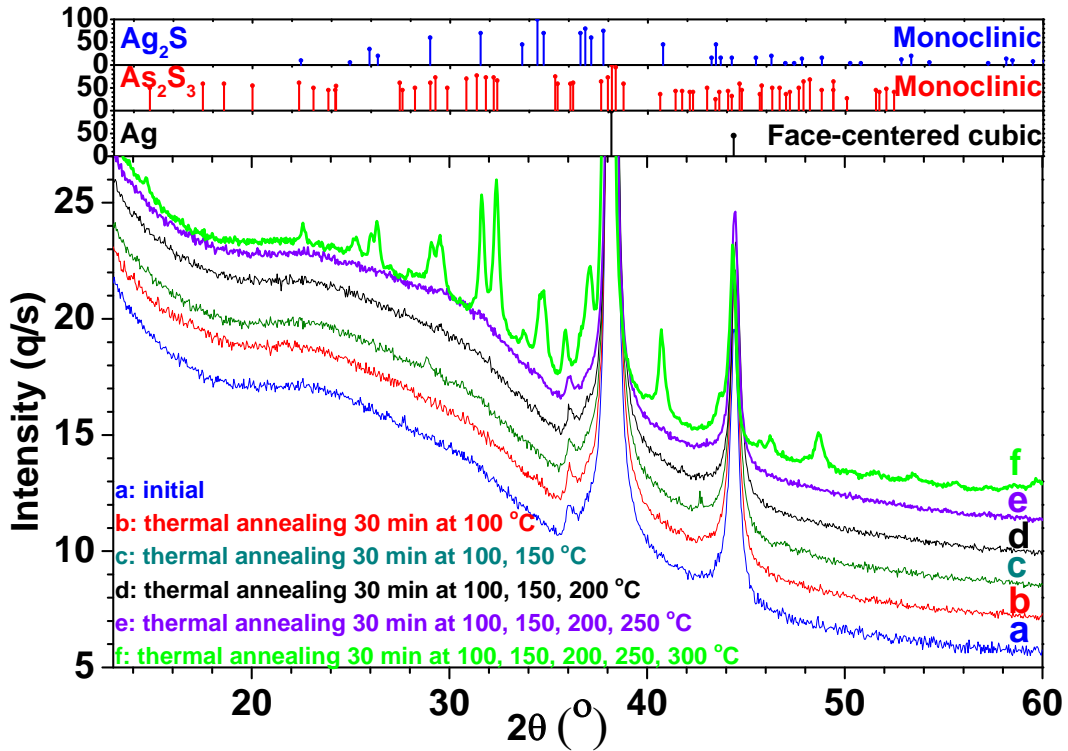


Fig. 1 The XRD diagrams of multilayer (4 x 2 layers) of Ag / As₂S₃ in initial state (a) and after 30 minutes of thermal annealing in nitrogen atmosphere at different temperatures (b ÷ f).

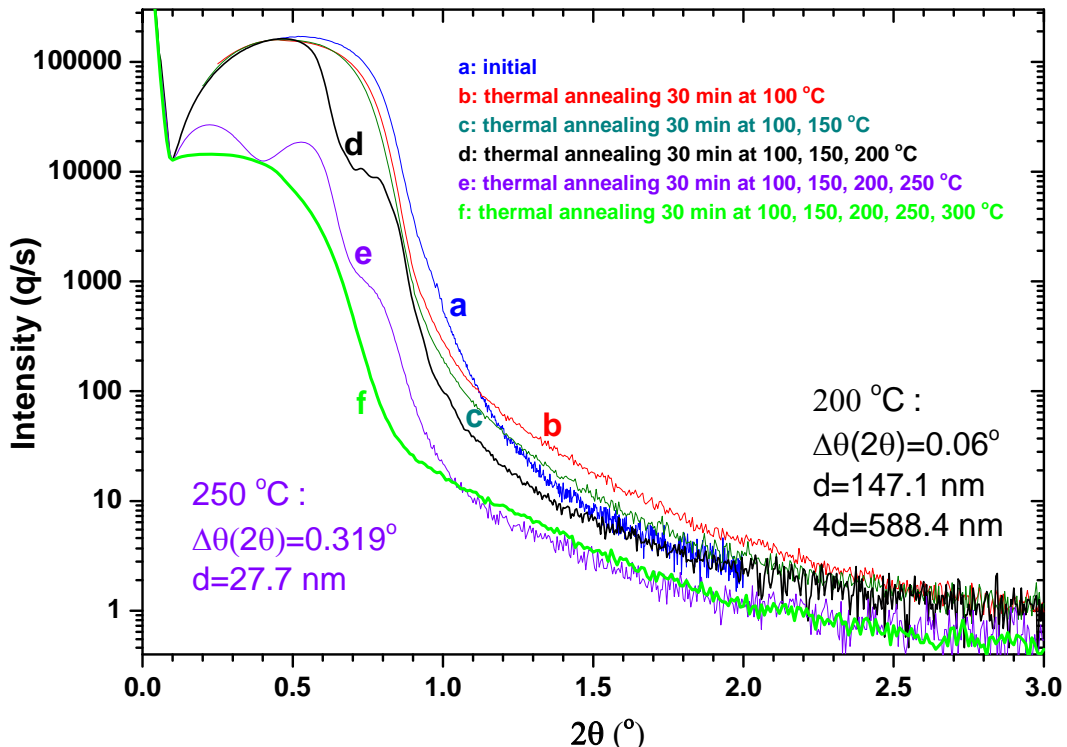


Fig. 2 The X-ray reflectivity (XRR) diagrams of the multilayer (4 x 2 layers) of Ag / As₂S₃ in initial state (a) and after 30 minutes of thermal annealing in nitrogen atmosphere at different temperatures (b ÷ f).

The transmission spectrum ($\lambda = 0.2 \div 2.1 \mu\text{m}$) of the multilayer sample (Fig. 3 b) changes significantly only after thermal annealing at 300 °C (fig. 3 f). One observes the gradual change of the optical transmission when the sample is annealed at increasing temperature. The optical

absorption edge shifts slowly to the higher wavelengths and the details of behaviour of the optical curve speak in the favour of the idea that the sample remains inhomogeneous even for the temperatures that overcome the crystallization point of the chalcogenide material that alternate with the layers of silver, although silver strongly diffuses in the film.

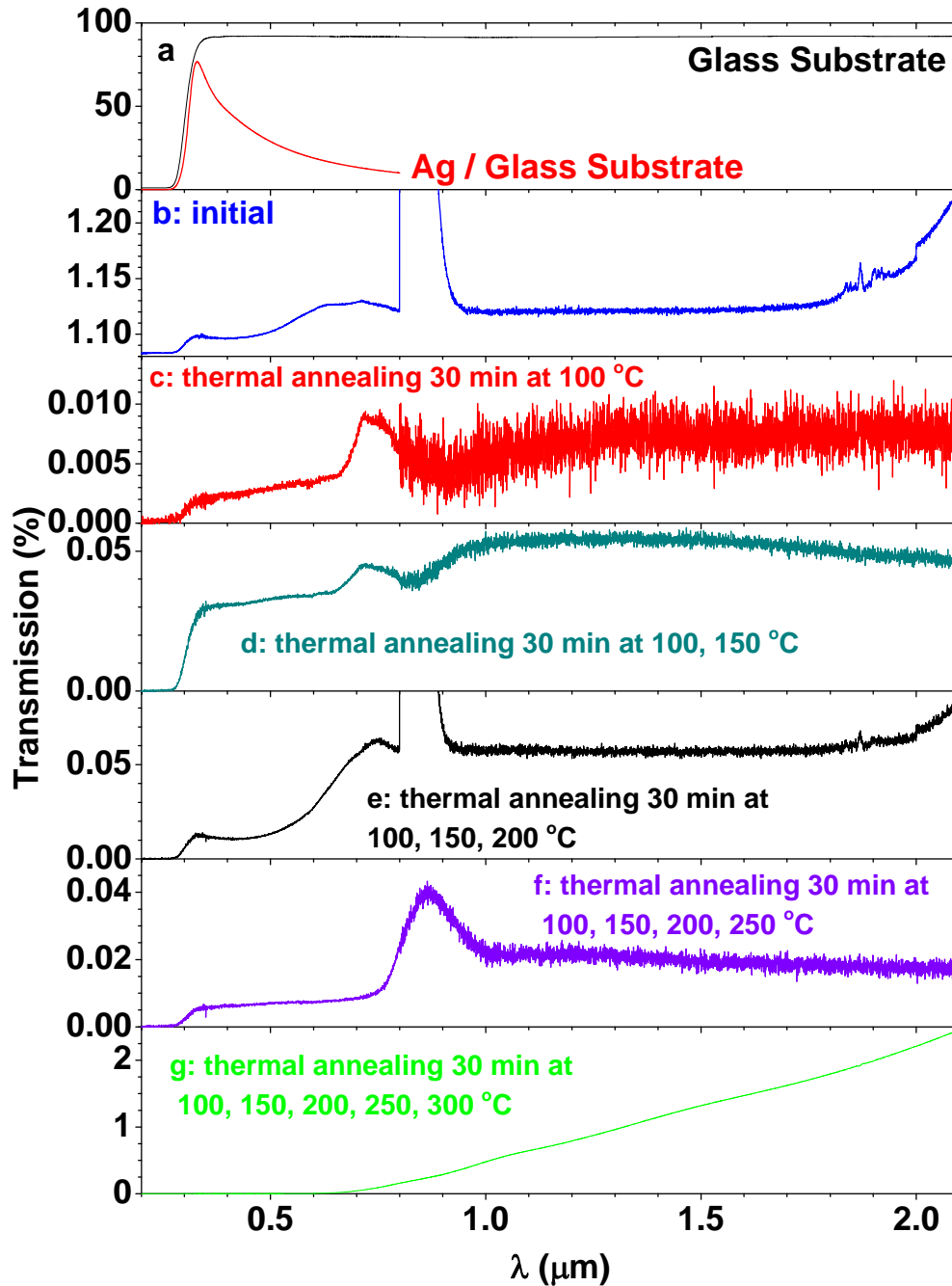


Fig. 3. The transmission spectrum of multilayer (4 x 2 layers) of Ag / As₂S₃ in initial state (b) and after 30 minutes of thermal annealing in nitrogen atmosphere at different temperatures (c ÷ g). The high increase of intensity in the region of 0.8 ÷ 0.9 μm wavelengths of b) and e) spectra is a spurious effect due to the change of the prism of the spectrometer.

4. Conclusions

A multilayer (4 x 2 layers) of Ag / As₂S₃ has been prepared and its stability against thermal annealing in nitrogen atmosphere for 30 minutes at different temperatures was tested. The multilayer is roughly stable up to 150 °C. After thermal annealing at 200 °C and 250 °C silver

diffuses more increasingly in As_2S_3 layers. After thermal annealing at 200 °C the thickness of the multilayer was estimated to be 588.4 nm. After thermal annealing at 250 °C at the surface of the sample a nanolayer with 27.7 nm thickness is formed. The crystallization of the films occurs after thermal annealing at 300 °C when the sample shows an XRR diagram corresponding to a thick monolayer. These crystalline phases could be Ag_2S and As_2S_3 . The optical transmission spectrum of the sample changes significantly only after thermal annealing at 300 °C.

Acknowledgement

The authors kindly acknowledge the financial support of the Ministry of National Education in the frame of the Project PN45-09.

References

- [1] J. Teteris, M. Reinfelde, *J. Optoelectron. Adv. Mater.* **5(5)**, 1355 (2003).
- [2] *Non-Crystalline Chalcogenides*, M. Popescu, Kluwer Academic Publishers, Dordrecht, 2000.
- [3] A. Kolobov, K. Tanaka, *Handbook on Advanced Electronic and Photonic Materials*, Academic Press, New York, 2000.
- [4] A. V. Kolobov, G. E. Bedelbaeva, *Philos. Mag. B* **64**, 21 (1991).
- [5] T. Wagner, M. Frumar, V. Suskova, *J. Non-Cryst. Solids* **128**, 197 (1991).
- [6] K. Tanaka, *J. Non-Cryst. Solids* **170**, 27 (1994).
- [7] A. V. Kolobov, *Photoinduced metastability in amorphous semiconductors*, Wiley-VCH Weinheim, 2003.
- [8] T. Kawaguchi, S. Maruno, S. R. Elliott, *J. Non-Cryst. Solids* **211**, 187 (1997).
- [9] A. Lorinczi, M. Popescu, F. Sava, A. Velea, I. D. Simandan, *Physica Status Solidi C* **8(9)**, 2617 (2011).
- [10] F. Sava, M. Popescu, A. Lorinczi, Alin Velea, Possible mechanism of Ag photodiffusion in a- As_2S_3 thin films, *Physica Status Solidi B* **250(5)**, 999-1003 (2013).
- [11] F. Jipa, M. Zamfirescu, Alin Velea, M. Popescu, R. Dabu, Femtosecond laser lithography in organic and non-organic materials, Chapter 13, InTech Publ. House, pp. 65-94, 2013.
- [12] J. Fick, B. Nicolas, C. Rivero, K. Elshot, R. Irwin, K.A. Richardson, M. Fischer, R. Vallée, Thermally activated silver diffusion in chalcogenide thin films, *Thin Solid Films* **418**, 215 (2002).
- [13] A. Zekak, P.J.S. Ewen, C.W. Slinger, A.E. Owen, The effect of heat on the metal photodissolution process in amorphous $\text{As}_{40}\text{S}_{60}$ films, *J. Non-Cryst. Solids* **202**, 122 (1996).
- [14] T. Wagner, *Journal of Optoelectronics and Advanced Materials* **4(3)**, 717 (2002).
- [15] M. Krbal, T. Wágner, M. Frumar, Mil. Vlček, B. Frumarová, *Physics and Chemistry of Glasses - European Journal of Glass Science and Technology Part B*, **47(2)**, 193 (2006).
- [16] T. Wágner, M. Krbal, J. Jedelský, Mil. Vlček, B. Frumarová, M. Frumar, *J. Optoelectron. Adv. Mater.* **7(1)**, 153 (2005)
- [17] Dezhi Qin, Guangrui Yanga, Guoxu He, Li Zhang, Qiuxia Zhang, Luyao Li, *Chalcogenide Letters*, Vol. 9 (11), Nov. 2012, p.441.
- [18] Sandeep Kumar, Digwijay Singh, R. Thangaraj, *Chalcogenide Letters*. **8(5)**, 335 (2011).
- [19] M. Pandiaranan, N. Soundararajan, C. Vijayan, *Journal of Ovonic Research*, **7(1)**, 21 (2011).
- [20] Kinga Krupa-Zuczek, Katarzyna Bialik-Was, Agnieszka Sobczak Kupiec, Marek Piatkowski, Malgorzata Zimowska, Bozena Tyliszczak, *Digest Journal of Nanomaterials and Biostructures* **6(4)**, 1725 (2011).